

This listing of claims will replace all prior versions,
and listings, of claims in the application:

LISTING OF CLAIMS:

Claims 1-6 (previously canceled).

Claim 7. (currently amended): A semiconductor device
comprising:

a substrate;

a first semiconductor chip on said substrate;

CI a second semiconductor chip overlying said first
semiconductor chip;

a wiring layer between said first and second
semiconductor chips, said wiring layer including a polyimide tape
having a copper foil layer ~~therein~~ therebetween;

a plurality of bonding pads on said wiring layer, said
substrate and said first and second semiconductor chips; and

a plurality of bonding wires for connecting said plural
bonding pads to each other,

~~wherein said second semiconductor chip is mounted on
said wiring layer by an adhesive material and said wiring layer is
provided on said first semiconductor chip without using an
adhesive material.~~

Claim 8. (previously amended): The semiconductor device according to claim 7, wherein,

a first bonding wire connects one of said plural bonding pads on said substrate to one of said plural bonding pads on said first semiconductor chip;

a second bonding wire connects one of said plural bonding pads on said substrate to one of said plural bonding pads on said wiring layer; and

CI
a third bonding wire connects said one of said plural bonding pads on said wiring layer to one of said plural bonding pads on said semiconductor substrate.

Claim 9. (previously added): The semiconductor device according to claim 7, further comprising a connection wire for connecting said one of said plural bonding pads on the wiring layer to another one of said plural bonding pads on said wiring layer.

Claim 10. (previously added): The semiconductor device according to claim 7, further comprising a via hole in said wiring layer, said via hole having a contact for connecting one of said plural bonding pads on the wiring layer to one of said plural bonding pads on said first semiconductor chip.

Claim 11. (previously added): The semiconductor device according to claim 9, further comprising a via hole in said wiring layer, said via hole having a contact for connecting yet another one of said plural bonding pads on the wiring layer to one of said plural bonding pads on said first semiconductor chip.

Claim 12. (currently amended) A semiconductor device comprising:

C'
a substrate;

a first semiconductor chip on said substrate;

a second semiconductor chip overlying said first semiconductor chip;

a wiring layer between said first and second semiconductor chips, said wiring layer including a conductor ~~within said wiring layer~~ laminated between polyimide layers;

a plurality of bonding pads on said wiring layer, said substrate and said first and second semiconductor chips; and

a plurality of bonding wires for connecting said plural bonding pads to each other,

wherein said second semiconductor chip is mounted on said wiring layer by an adhesive material and said wiring layer is provided on said first semiconductor chip without using an adhesive material.

Claim 13. (previously added) The semiconductor device according to claim 12, wherein said conductor comprises first and second pads on said wiring layer connected by a connection wire.

Claim 14. (previously amended) The semiconductor device according to claim 12, wherein

C' a first bonding wire connects one of said plural bonding pads on said substrate to one of said plural bonding pads on said first semiconductor chip;

a second bonding wire connects one of said plural bonding pads on said substrate to one of said plural bonding pads on said wiring layer; and

a third bonding wire connects another one of said plural bonding pads on said wiring layer to one of said plural bonding pads on said semiconductor substrate,

said second and third bonding wire being electrically connected through said conductor.

Claim 15. (previously added): The semiconductor device according to claim 12, wherein said wiring layer comprises a lamination of polyimide layer and an aluminum layer.

Claim 16. (previously added): The semiconductor device according to claim 12, further comprising a via hole in said wiring layer, said via hole having a contact for connecting one

of said plural bonding pads on the wiring layer to one of said plural bonding pads on said first semiconductor chip.

Claim 17. (currently amended): A semiconductor device comprising:

a substrate;

a first semiconductor chip on said substrate;

a second semiconductor chip overlying said first semiconductor chip;

CI a wiring layer between said first and second semiconductor chips, said wiring layer including a an inner layer conductor traversing said wiring layer;

a plurality of bonding pads on said wiring layer, said substrate and said first and second semiconductor chips; and

a plurality of bonding wires for connecting said plural bonding pads to each other,

~~wherein said second semiconductor chip is mounted on said wiring layer by an adhesive material and said wiring layer is provided on said first semiconductor chip without using an adhesive material.~~

Claim 18. (previously added): The semiconductor device according to claim 17, further comprising a via hole in said wiring layer, said via hole having a contact for connecting one of

said plural bonding pads on the wiring layer to one of said plural bonding pads on said first semiconductor chip.

Claim 19. (previously added): The semiconductor device according to claim 17, wherein said conductor comprises first and second pads on said wiring layer connected by a connection wire.

Claim 20. (currently amended): A semiconductor device comprising:

a substrate;

a first semiconductor chip on said substrate;

a second semiconductor chip overlying said first semiconductor chip;

a wiring layer between said first and second semiconductor chips, said wiring layer including a polyimide tape having a copper foil layer ~~therein~~ therebetween;

a plurality of bonding pads on said wiring layer, said substrate and said first and second semiconductor chips;

a plurality of bonding wires for connecting said plural bonding pads to each other; and

a via hole in said wiring layer, said via hole having a contact for connecting one of said plural bonding pads on the wiring layer to one of said plural bonding pads on said first semiconductor chip,

C1 wherein said second semiconductor chip is mounted on said wiring layer by an adhesive material and said wiring layer is provided on said first semiconductor chip without using an adhesive material.

Claim 21. (previously added): The semiconductor device according to claim 20, further comprising a connection wire for connecting said one of said plural bonding pads on the wiring layer to another one of said plural bonding pads on said wiring layer.
